

isc Silicon NPN Darlington Power Transistor

MJH11022

DESCRIPTION

- Collector-Emitter Sustaining Voltage : V_{CEO(SUS)}= 250V (Min.)
- High DC Current Gain
- : h_{FE}= 400(Min.)@I_C= 10A
- Low Collector Saturation Voltage
- : V_{CE (sat)}= 1.0V(Max.)@ I_C= 5.0A
- Complement to Type MJH11021
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

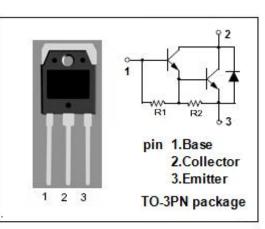
• Designed for general purpose amplifiers, low frequency switching and motor control applications.

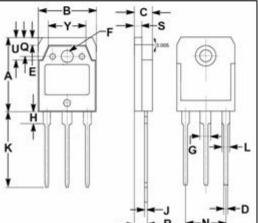
or-Base Voltage or-Emitter Voltage Base Voltage or Current-Continunous or Current-Peak	250 250 5 15 30	V V V A A
-Base Voltage or Current-Continunous or Current-Peak	5 15 30	V A
or Current-Continunous or Current-Peak	15	A
or Current-Peak	30	
		A
umant Cantinumaus		
urrent-Continunous	0.5	A
or Power Dissipation 5℃	150	W
n Temperature	150	°C
e Temperature Range	-65~150) °C
	n Temperature	n Temperature 150

ABSOLUTE MAXIMUM RATINGS (Ta=25℃)

SYMBOLPARAMETERMAXUNITRth j-cThermal Resistance, Junction to Case0.833°C/W

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	mm	
DIM	MIN	MAX
Α	19.60	20.30
В	15.50	15.70
С	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
κ	19.80	20.70
L	1.90	2.20
Ν	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

isc website: www.iscsemi.com



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ELECTRICAL CHARACTERISTICS

$T_{\text{c}}\text{=}25^{\circ}\!\!\!^{\circ}\!\!^{\circ}_{\circ}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	МАХ	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C = 30mA; I _B = 0	250		V
V _{CE(sat)-1}	Collector-Emitter Saturation Voltage	I _C = 10A; I _B = 0.1A		2.5	V
V _{CE(sat)-2}	Collector-Emitter Saturation Voltage	I _C = 15A; I _B = 0.15A		4.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 15А; I _в = 0.15А		3.8	V
V _{BE} (on)	Base-Emitter On Voltage	I _C = 10A, V _{CE} = 5V		2.8	V
I _{CBO}	Collector Cutoff Current	V _{CB} =250V;I _E =0		0.5	mA
I _{CEO}	Collector Cutoff Current	V _{CE} = 125V; I _B = 0		1.0	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0		2.0	mA
h _{FE-1}	DC Current Gain	I _C = 10A, V _{CE} = 5V	400	15000	
hfe-2	DC Current Gain	I _C = 15A, V _{CE} = 5V	100		

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